



제 31회 한국반도체학술대회

The 31st Korean Conference on Semiconductors

2024년 1월 24일(수)-26일(금) | 경주화백컨벤션센터(HICO)

2024년 1월 26일(금), 09:00-10:45

Room D(104), 1층

F. Silicon and Group-IV Devices and Integration Technology 분과

[FD1-F] Advanced Integration Technology

좌장: 백명현 교수(강릉원주대학교), 우성윤 교수(경북대학교)

<p>FD1-F-1 09:00-09:15</p>	<p>Heterogeneous 3D Vertical Inverter of MoS₂ nFET on Si pMOSFET Using Sequential Fabrication Process Boncheol Ku¹, Shanmukh Kutagulla², Deji Akinwande², and Changhwan Choi¹ ¹Division of Materials Science and Engineering, Hanyang University, ²The Department of Electrical and Computer Engineering, The University of Texas at Austin</p>
<p>FD1-F-2 09:15-09:30</p>	<p>Impact of Low-temperature Deuterium Annealing for Poly-Si Channel Thin-Film Transistors Tae-Hyun Kil, Ju-Won Yeon, Hyo-Jun Park, and Jun-Young Park Chungbuk National University</p>
<p>FD1-F-3 09:30-09:45</p>	<p>그린 레이저를 이용한 모놀리식 3D 소자 제작 공정에서 상부 게이트 버퍼층 삽입을 통한 MOSFET 성능 개선 박영근, 정재중, 김희태, 김성호, 김동빈, 추준홍, 강창연, 조병진 한국과학기술원 전기 및 전자공학부</p>
<p>FD1-F-4 09:45-10:00</p>	<p>Simulation of Monolithic CFET Using In-house TCAD Process Emulator Seung-Woo Jung, In Ki Kim, Kwang-Woon Lee, and Sung-Min Hong School of Electrical Engineering and Computer Science, GIST</p>
<p>FD1-F-5 10:00-10:15</p>	<p>Numerical Simulation of Bottom Dielectric Isolated (BDI) Forksheet Field Effect Transistor (FSFET) with In-House TCAD Process Emulator and Device Simulator In Ki Kim and Sung-Min Hong School of Electrical Engineering and Computer Science, Gwangju Institute of Science and Technology</p>
<p>FD1-F-6 10:15-10:30</p>	<p>Monolithic 3-dimensional Static Random Access Memory Array Cell Consisting of Feedback Field-effect Transistor for Memory System Jong Hyeok Oh and Yun Seop Yu Major of ICT & Robotics Eng., Hankyong National University</p>



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FD1-F-7

10:30-10:45

Thickness Scaling of Ferroelectric HfZrO_2 and Its Reliability on Germanium Substrate

Jai-Youn Jeong^{1,2}, Changhwan Shin², and Jae-Hoon Han¹

¹Center for Opto-electronic Materials and Devices, KIST, ²Device and Circuit Laboratory, Korea University